

### **Power Semiconductor Technology**

# SPSD2030 Schottky Power Rectifier

**SPSD2030** 

# Schottky Power Rectifier D<sup>2</sup>PAK Power Package

Schottky Barrier Rectifier 20.0 Ampers 30 Volts

### Features

- Metal silicon junction, majority carrier conduction
- · Highly stable oxide passivated junction
- Guardring for stress protection
- · Low forward voltage drop.
- High current capability
- High surge capability
- · High reliability
- · Ideal for solar panel PV application such as By-Pass diode

### Mechanical Data

Cases: D<sup>2</sup>PAK, Epoxy, Molded

Current at Rated DC Blocking

Storage Temperature Range

In DC Forward Mode

Operating Junction Temperature

Typical Thermal Resistance (Note 2)

Voltage (Note1)

- Plastic package has Underwriters Laboratory Flammability Classification 94V-0
- Terminals : All Terminal Leads are Readily Solderable

Maximum Ratings and Electrical Characteristics

- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- Weight : 1.7 grams

# 

Units
Volts
Volts
Volts

Amps

**Amps** 

Volts

mΑ

°C/W

°C

°C

°C

50.0

1.5

-65 to +150

-50 to +200

200 max

(Per Diode Leg, Ta = 25°C unless ot	herwise note	ed)		
Parameter		Symbols	SPSD2030	
Maximum Repetitive Reverse Voltage		$V_{RRM}$	30	
Maximum RMS Voltage		$V_{RMS}$	21	
Maximum DC Blocking Voltage		$V_{DC}$	30	
Maximum average forward rectified current (see Fig. 1)		I <sub>(AV)</sub>	10.0	
Non-repetitive Peak Forward Surge Current 8.3 ms Single Half-Sine-Wave		I <sub>FSM</sub>	200.0	
Maximum Instantaneous Forward Voltage @ 10A (Note 1)		V <sub>F</sub>	0.5	
Maximum Instantaneous Reverse	Ta = 25°C		0.5	

Ta = 100°C

Notes: 1. Pulse test with PW=300 usec, 1% duty cycle.

2. Thermal resistance junction to case.

### http://www.sipower-inc.com

 $R_{\theta JC}$ 

 $\mathsf{T}_{\mathsf{stg}}$ 

 $T_{J}$ 

 $T_{\rm J}$ 



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